

PATENT ABSTRACTS OF JAPAN

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(54) NONPOLLUTING METHOD OF GAS FOR SEMICONDUCTOR

(57)Abstract:

PURPOSE: To remove harmful gases for semiconductors virtually perfectly by absorbing the gases for semiconductors by using a rotary type fine foam generator and using aqueous alkali hydroxide soln. contg. inorg. salts as absorbing liquid.

CONSTITUTION: Gases for semiconductors such as silane, arsine, and phosphine are absorbed and removed by using aqueous alkali hydroxide soln. contg. inorg. salts as absorbing liquid and using a rotary type fine foam generator. For example, 5.5l water is put into a "Rotary Atomizer Model TOPCA-L-2" and further 120g NaCl and 40g NaOH are put therein and these are dissolved. While a rotor is being rotated at 2,500 revolutions per minute, pure silane was introduced at the rate of 0.2W2.5l/min, but the phenomena such as explosion and combustion at the gas releasing port were not observed. Suitable concn. of inorg. salts in the absorbing liquid is 0.5W20wt%, and the suitable concn. of the aqueous alkali hydroxide soln. is 0.2W10.0wt%.

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